

GaAs-IR-Lumineszenzdiode
GaAs Infrared Emitter
Lead (Pb) Free Product - RoHS Compliant

SFH 4511



Wesentliche Merkmale

- GaAs-LED mit sehr hohem Wirkungsgrad
- 5mm Kunststoffgehäuse
- Peakwellenlänge 950 nm
- Sehr enger Abstrahlwinkel ($\pm 4^\circ$)
- Hohe Strahlstärke
- Hohe Zuverlässigkeit

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Sensorik
- Diskrete Lichtschranken

Features

- Very highly efficient GaAs-LED
- 5mm plastic package
- Peak Wavelength 950 nm
- Very narrow radiation Angle (± 4 Deg.)
- High radiant intensity
- High reliability

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Sensor technology
- Discrete interrupters

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 100$ mA, $t_p = 20$ ms) Radiant Intensity Grouping ¹⁾ I_e (mW/sr)
SFH 4511	Q62702Q5557	> 63 (typ. 150)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.001$ sr / measured at a solid angle of $\Omega = 0.001$ sr

Grenzwerte ($T_A = 25^\circ\text{C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{\text{op}}; T_{\text{stg}}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlassstrom Forward current	I_F	100	mA
Stoßstrom, $t_p = 10 \mu\text{s}, D = 0$ Surge current	I_{FSM}	3	A
Verlustleistung Power dissipation	P_{tot}	165	mW
Wärmewiderstand Thermal resistance	R_{thJA}	450	K/W

Kennwerte ($T_A = 25^\circ\text{C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100 \text{ mA}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	φ	± 4	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm^2
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm^2
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100 \text{ mA}, R_L = 50 \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100 \text{ mA}, R_L = 50 \Omega$	t_r, t_f	0.5	μs

Kennwerte ($T_A = 25^\circ\text{C}$)**Characteristics (cont'd)**

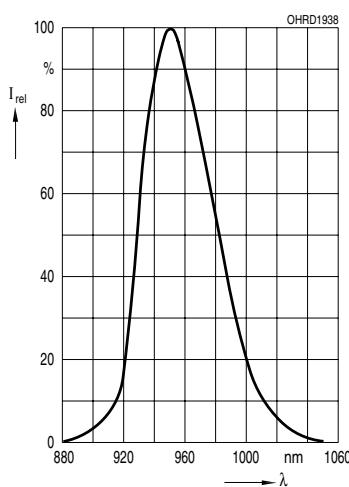
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kapazität, Capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_o	25	pF
Durchlassspannung Forward voltage $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ $I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	V_F V_F	1.3 (≤ 1.5) 2.3 (≤ 2.8)	V V
Sperrstrom Reverse current $V_R = 5 \text{ V}$	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	Φ_e	22	mW
Strahlstärke Radiant intensity $I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	$I_e \text{ typ.}$	1200	mW/sr
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100 \text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100 \text{ mA}$	TC_I	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100 \text{ mA}$ Temperature coefficient of V_F , $I_F = 100 \text{ mA}$	TC_V	- 2	mV/K
Temperaturkoeffizient von λ , $I_F = 100 \text{ mA}$ Temperature coefficient of λ , $I_F = 100 \text{ mA}$	TC_λ	+ 0.3	nm/K

Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.001 \text{ sr}$ **Grouping of Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.001 \text{ sr}$

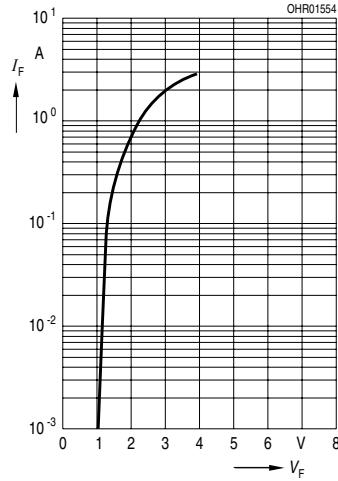
Bezeichnung Parameter	Symbol	Wert Value	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	I_e min. I_e typ.	63 150	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1 \text{ A},$ $t_p = 100 \mu\text{s}$	I_e typ.	1200	mW/sr

Relative Spectral Emission

$$I_{\text{rel}} = f(\lambda)$$

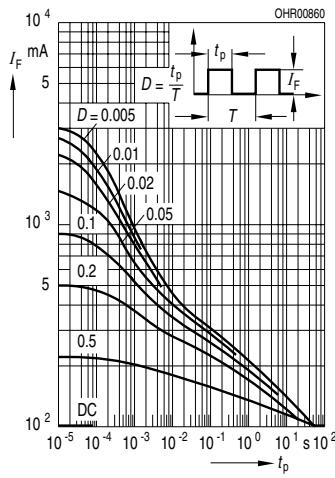
**Forward Current**

$$I_F = f(V_F), \text{ single pulse, } t_p = 20 \mu\text{s}$$

**Permissible Pulse Handling Capability**

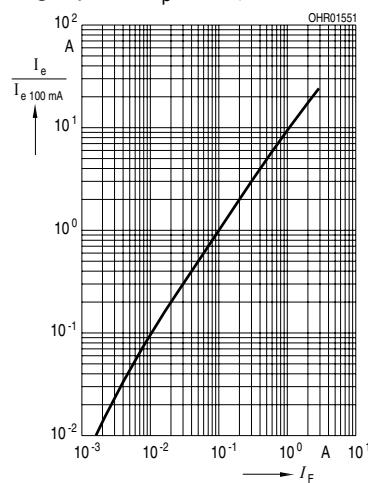
$$I_F = f(\tau), T_A = 25^\circ\text{C}$$

duty cycle $D = \text{parameter}$

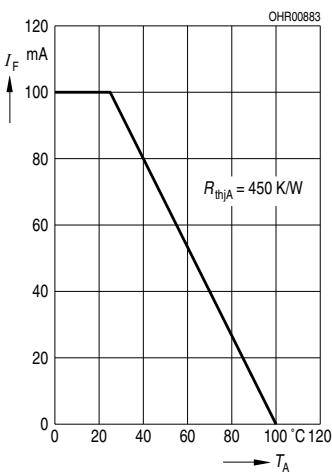
**Radiant Intensity**

$$\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$$

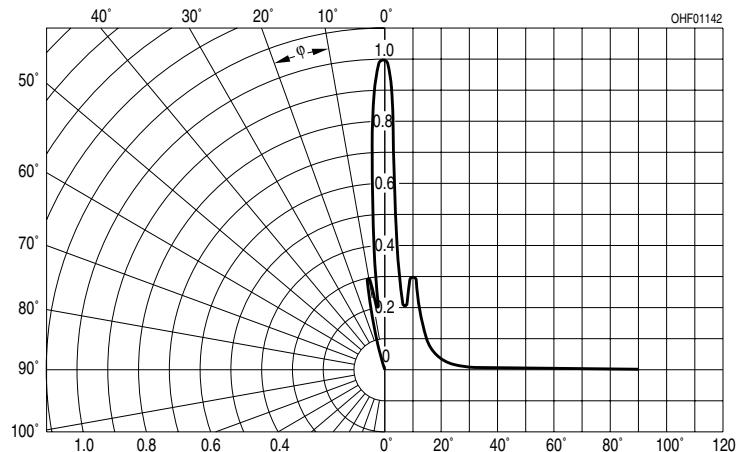
Single pulse, $t_p = 20 \mu\text{s}$

**Max. Permissible Forward Current**

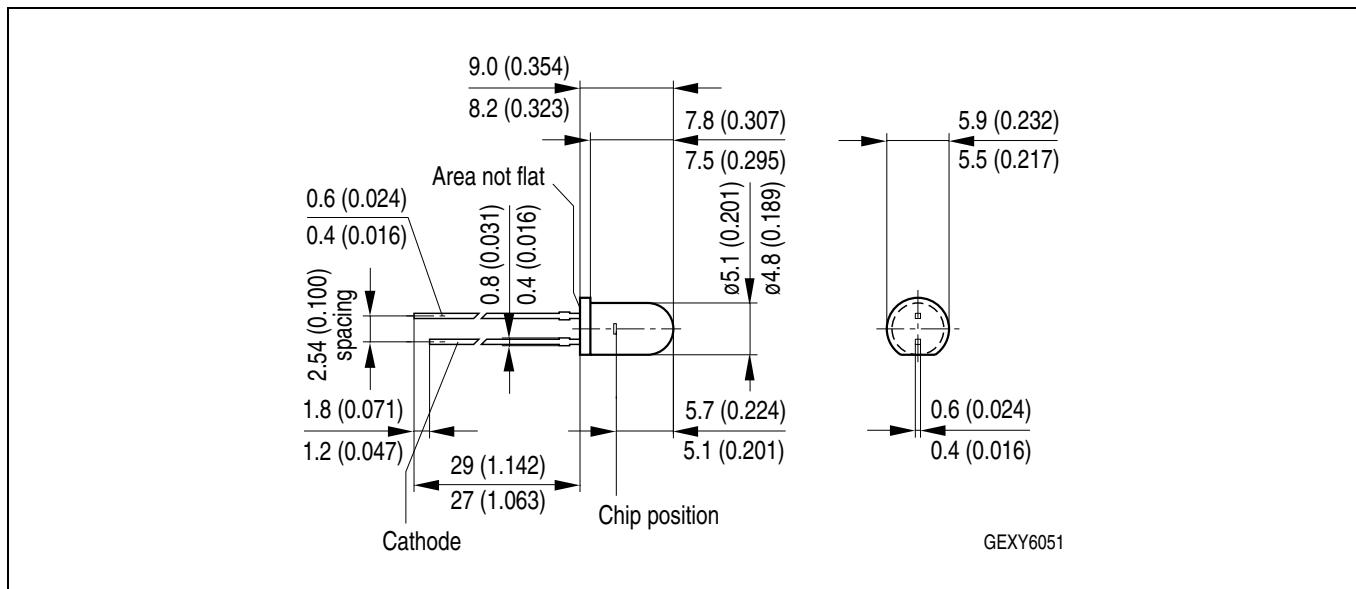
$$I_F = f(T_A)$$

**Radiation Characteristics,**

$$I_{\text{rel}} = f(\phi)$$



Maßzeichnung
Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

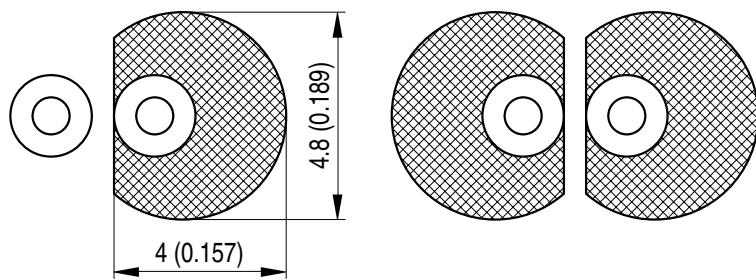
Package	5 mm radial (T 1 $\frac{3}{4}$)
Colour	black

Empfohlenes Lötpaddesign

Recommended Solder Pad

Wellenlöten (TTW)

TTW Soldering

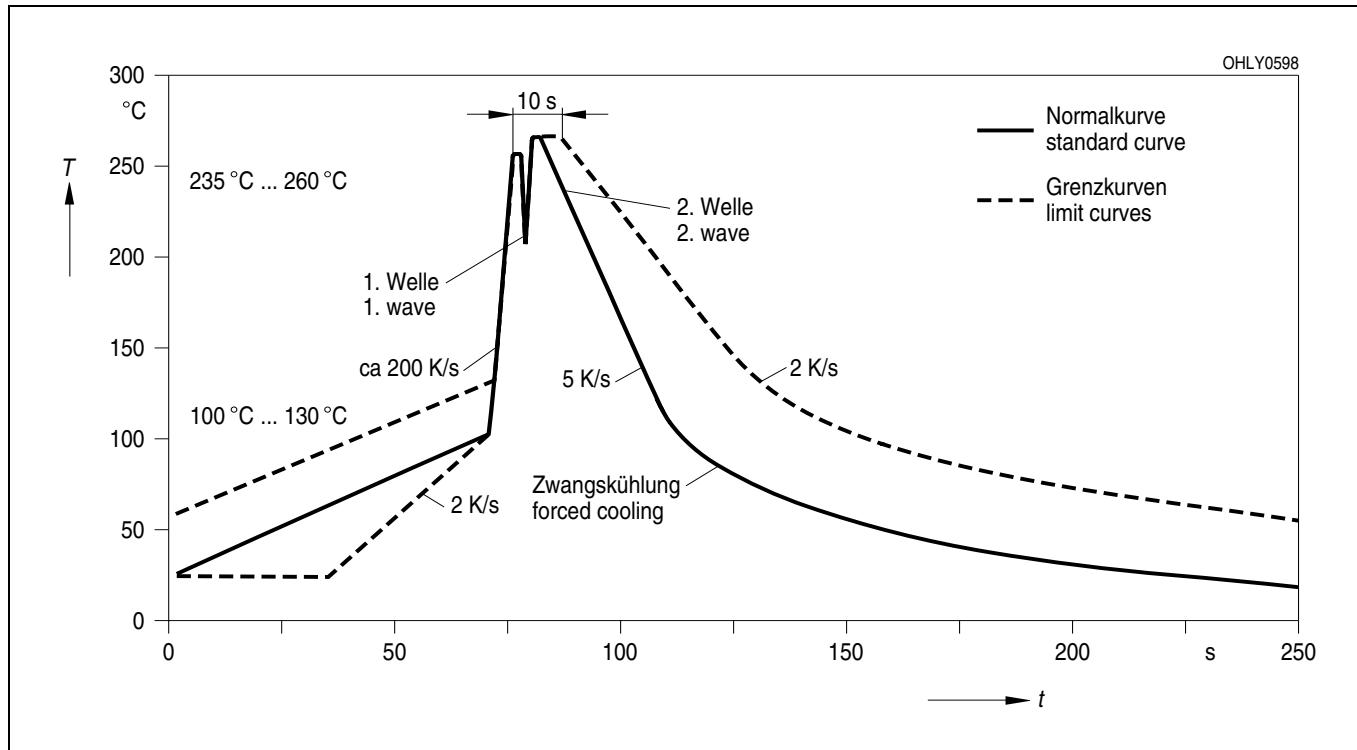


OHLPY985

Maße in mm (inch) / Dimensions in mm (inch).

Lötbedingungen Soldering Conditions Wellenlöten (TTW) TTW Soldering

(nach CECC 00802)
(acc. to CECC 00802)



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